IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): An epoxy resin composition for semiconductor encapsulating ~~consisting essentially of~~ comprising:

an epoxy resin,

a phenol resin,

an inorganic filler,

a curing accelerator, and

a carbon precursor having a specific electric resistivity in a semiconductor region of 1 $\times 10^4$ $\Omega \cdot$cm or more but ~~less than 1×10^7~~ not more than 10^6 $\Omega \cdot$cm, wherein ~~the~~ amounts of the inorganic filler and the carbon precursor in the epoxy resin composition are respectively 65-92 wt% and 0.1-5.0 wt%.

Claim 2 (Previously Presented): The epoxy resin composition for semiconductor encapsulating according to claim 1, wherein the carbon precursor has an H/C ratio by weight determined by elemental analysis of 2/97 to 4/93.

Claim 3 (Previously Presented): The epoxy resin composition for semiconductor encapsulating according to claim 1, wherein the carbon precursor is fine particles having an average particle diameter of 0.5-50 μm.

Claim 4 (Previously Presented): The epoxy resin composition for semiconductor encapsulating according to claim 1, wherein the carbon precursor is fine particles having an average particle diameter of 0.5-20 μm.

Claim 5 (Canceled)

Claim 6 (Previously Presented): The epoxy resin composition for semiconductor encapsulating according to claim 1, wherein the amount of the inorganic filler in the total amount of the epoxy resin composition is 70-91 wt%.

Claim 7 (Previously Presented): The epoxy resin composition for semiconductor encapsulating according to claim 1, wherein the carbon precursor is produced by carbonizing a phenol resin at a calcination temperature of 600-650°C.

Claim 8 (Previously Presented): A semiconductor device comprising a semiconductor element encapsulated using the epoxy resin composition for semiconductor encapsulating according to any one of claims 1-4, 6 and 7.